Silicon Photodiode in Top-View PLCC-2 Package

OP980

Features:

- Wide acceptance angle, 100°
- Fast response time
- Linear response vs Irradiance •
- Plastic leadless chip carrier (PLCC-2) .
- Low Capacitance •
- **Top Sensing Area**
- Tape and reel packaging
- Moisture Sensitivity Level: MSL2 or >

Description:

The **OP980** is a high speed, low-noise and high sensitivity PIN silicon photodiode mounted in a miniature SMD package. The device has a flat window lens, which enables a wide acceptance angle at 100°. Due to its clear lens, the OP980 responds to visible and near infrared light. It is packaged in a plastic leadless chip carrier that is compatible with most automated pick and place mounting equipment. The OP980 is mechanically and spectrally matched to the OP280 and OP180 infrared LED.

Applications:

- Non-contact position sensing •
- Datum detection .
- Computer peripherals
- Smoke detectors
- **Touch Sensors**

Package Outline Dimensions

- Machine automation
- Optical encoders
- Reflective sensors
- Counters and sorters
- Miniature optical switches

Ordering Information								
Part Number	Sensor	Viewing Angle						
OP980	Photodiode	100°						



General Note

RoHS

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

OPTEK Technology, Inc. 1645 Wallace Drive, Carrollton, TX 75006lPh: +1 972 323 2200 www.optekinc.com l www.ttelectronics.com







Τт

Electronics

Silicon Photodiode in Top-View

PLCC-2 Package



OP980

Operating Temperature Range -25° C Lead Soldering Temperature Electrical Characteristics ($T_A \approx 25^\circ$ C unless otherwise noted) SYMBOL PARAMETER MIN TYP MAX UNITS TEST CONDITIONS IL Light Current 0.5 - - μA $V_R = 5.0 \text{ V}, E_E = 1.0 \text{ mW/cm}^2$ ID Dark Current - - 60 nA $V_R = 30.0 \text{ V}, E_E = 0.0 \text{ mW/cm}^2$ VR(BR) Reverse Breakdown Voltage 60 - V I_R = 10 μA										
Operating Temperature Range -25° C Lead Soldering Temperature Electrical Characteristics ($T_A = 25^\circ$ C unless otherwise noted) MIN TYP MAX UNITS TEST CONDITIONS SYMBOL PARAMETER MIN TYP MAX UNITS TEST CONDITIONS I_L Light Current 0.5 - - μA $V_R = 5.0 \text{ V}, E_E = 1.0 \text{ mW/cm}^2$ I_D Dark Current - - 60 nA $V_R = 30.0 \text{ V}, E_E = 0.0 \text{ mW/cm}^2$ VR _(BR) Reverse Breakdown Voltage 60 - - V I_R = 10 \mu A V_F Forward Voltage - - 1.2 V I_F = 1 mA, Ee = 0.0 mW/cm^2	Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)									
Lead Soldering Temperature Lead Soldering Temperature Electrical Characteristics ($T_A = 25^\circ$ C unless otherwise noted) SYMBOL PARAMETER MIN TYP MAX UNITS TEST CONDITIONS IL Light Current 0.5 - - μ A $V_R = 5.0 \text{ V}, E_E = 1.0 \text{ mW/cm}^2$ ID Dark Current - - 60 nA $V_R = 30.0 \text{ V}, E_E = 0.0 \text{ mW/cm}^2$ VR(BR) Reverse Breakdown Voltage 60 - - V I_R = 10 μ A VF Forward Voltage - - 1.2 V I_F = 1 mA, Ee = 0.0 mW/cm^2	torage T	-40° C to +100° C								
Electrical Characteristics (T_A = 25° C unless otherwise noted)SYMBOLPARAMETERMINTYPMAXUNITSTEST CONDITIONS I_L Light Current0.5 μA $V_R = 5.0 \text{ V}, E_E = 1.0 \text{ mW/cm}^2$ I_D Dark Current60nA $V_R = 30.0 \text{ V}, E_E = 0.0 \text{ mW/cm}^2$ $VR_{(BR)}$ Reverse Breakdown Voltage60V $I_R = 10 \mu A$ V_F Forward Voltage1.2V $I_F = 1 \text{ mA}, Ee = 0.0 \text{ mW/cm}^2$	Dperating	-25° C to +85° C								
SYMBOLPARAMETERMINTYPMAXUNITSTEST CONDITIONS I_L Light Current0.5 μA $V_R = 5.0 \text{ V}, E_E = 1.0 \text{ mW/cm}^2$ I_D Dark Current60nA $V_R = 30.0 \text{ V}, E_E = 0.0 \text{ mW/cm}^2$ $VR_{(BR)}$ Reverse Breakdown Voltage60V $I_R = 10 \mu A$ V_F Forward Voltage-1.2V $I_F = 1 \text{ mA}, Ee = 0.0 \text{ mW/cm}^2$	ead Sold	260° C ⁽¹⁾								
ILLight Current0.5- μ A $V_R = 5.0 \text{ V}, E_E = 1.0 \text{ mW/cm}^2$ IDDark Current60nA $V_R = 30.0 \text{ V}, E_E = 0.0 \text{ mW/cm}^2$ $VR_{(BR)}$ Reverse Breakdown Voltage60VI_R = 10 μ A V_F Forward Voltage1.2VI_F = 1 mA, Ee = 0.0 mW/cm^2	Electrical Characteristics (T _A ≈ 25° C unless otherwise noted)									
IDDark Current60nA $V_R = 30.0 \text{ V}, E_E = 0.0 \text{ mW/cm}$ $VR_{(BR)}$ Reverse Breakdown Voltage60V $I_R = 10 \mu A$ V_F Forward Voltage1.2V $I_F = 1 \text{ mA}, \text{ Ee} = 0.0 \text{ mW/cm}^2$	BOL	PARAMETER	MIN	ТҮР	МАХ	UNITS	TEST CONDITIONS			
VR(BR)Reverse Breakdown Voltage60-VIR = 10 μ AVFForward Voltage1.2VIF = 1 mA, Ee = 0.0 mW/cm ²	Lię	Light Current	0.5	-	-	μA	$V_{R} = 5.0 \text{ V}, \text{ E}_{E} = 1.0 \text{ mW/cm}^{2(3)}$			
V _F Forward Voltage - 1.2 V I _F = 1 mA, Ee = 0.0 mW/cm ²	Da Da	Dark Current	-	-	60	nA	$V_{R} = 30.0 \text{ V}, E_{E} = 0.0 \text{ mW/cm}^{2(3)}$			
	_(BR) Re	Reverse Breakdown Voltage	60	-	-	V	I _R = 10 μA			
$\lambda_{\rm pk}$ Peak Sensitivity Wavelength - 890 - nm $V_{\rm R}$ = 5.0	F FO	Forward Voltage	-	-	1.2	V	$I_{F} = 1 \text{ mA}, \text{ Ee} = 0.0 \text{ mW/cm}^{2}$			
	_{ok} Pe	Peak Sensitivity Wavelength	-	890	-	nm	V _R = 5.0			
tr Rise Time - 50 - ns $V_R = 5.0, R_L = 1k$	r Ris	Rise Time	-	50	-	ns	$V_{R} = 5.0, R_{L} =$	1k		
tf Fall Time - 50 - ns $V_R = 5.0, R_L = 1k$	f Fa	Fall Time	-	50	-	ns	V _R = 5.0, R _L = 1k			

Notes:

- 1. Solder time less than 5 seconds at temperature extreme.
- 2. Derate linearly at 1.33 mW/° C above 25° C.
- 3. $E_{e(APT)}$ is an unfiltered GaAlAs LED with peak emission wavelength of 890nm. The measurement of the apertured radiant incidence upon a sensing area 0.081" (2.06mm) in diameter, perpendicular to and centered on the mechanical axis of the lens, and 0.590" (14.99mm) from the measurement surface. Measurement surface will be considered the tip of the top-view lens. $E_{e(APT)}$ is not necessarily uniform within the measured area.



Electrical Characteristic Performance Curves

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

General Note

Silicon Photodiode in Top-View PLCC-2 Package



OP980

More Typical Performance Curves



Total Capacitance $-C_T(pF)$ vs. Reverse Bias Voltage $-V_R(V)$

Reverse Voltage—V_R(V)



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

Silicon Photodiode in Top-View



PLCC-2 Package

OP980



Dimensions are in: mm Tolerance: ±0.01

Silicon Photodiode in Top-View

PLCC-2 Package



OP980

Taping and Orientation

- Reels come in quantity of 2000 units.
- Reel diameter is 180mm.



Tape Feed Direction



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.